

Ji-Hui Yang

List of Publications by Year in descending order

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papers

4,770
citations

279701

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315616

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docs citations

39
times ranked

6877
citing authors

#	ARTICLE	IF	CITATIONS
1	Semiconductor-to-metal transition from monolayer to bilayer blue phosphorous induced by extremely strong interlayer coupling: a first-principles study. <i>Nanoscale</i> , 2022, 14, 4082-4088.	2.8	3
2	Enhancing Hole Density and Suppressing Recombination Centers through Illumination in Kesterite Thin Film Solar Cells. <i>Journal of Physical Chemistry Letters</i> , 2022, 13, 2474-2478.	2.1	3
3	Computational Study of the $C_{2}P_{4}$ Monolayer as a Stable Two-Dimensional Material with High Carrier Mobility: Implications for Nanoelectronic Devices. <i>ACS Applied Nano Materials</i> , 2022, 5, 6972-6979.	2.4	4
4	Semiconducting $\hat{\Gamma}$ - $\hat{\Gamma}$ -boron sheet with high mobility and low all-boron contact resistance: a first-principles study. <i>Nanoscale</i> , 2021, 13, 8474-8480.	2.8	15
5	Dimensionality-Inhibited Chemical Doping in Two-Dimensional Semiconductors: The Phosphorene and MoS_{2} from Charge-Correction Method. <i>Nano Letters</i> , 2021, 21, 6711-6717.	4.5	14
6	Unusual defect properties in multivalent perovskite $Cs_{2}Mg_{6}I_{6}$: A first-principles study. <i>Physical Review Materials</i> , 2021, 5, .	0.9	3
7	Unusual interlayer coupling in layered Cu-based ternary chalcogenides $CuMCh_{2}$ (M = Sb, Tl). <i>Journal of Applied Physics</i> , 2021, 124, 074301.	2.8	14
8	Fully Boron-Sheet-Based Field Effect Transistors from First-Principles: Inverse Design of Semiconducting Boron Sheets. <i>Journal of Physical Chemistry Letters</i> , 2021, 12, 576-584.	2.1	14
9	Self-consistently determining structures of charged defects and defect ionization energies in low-dimensional semiconductors. <i>Physical Review B</i> , 2020, 102, .	1.1	9
10	Stacking induced indirect-to-direct bandgap transition in layered group-IV monochalcogenides for ideal optoelectronics. <i>Journal of Materials Chemistry C</i> , 2019, 7, 11858-11867.	2.7	10
11	Cu-Zn disorder in stoichiometric and non-stoichiometric $Cu_{2}ZnSnS_{4}/Cu_{2}ZnSnSe_{4}$. <i>AIP Advances</i> , 2019, 9, .	0.6	11
12	Two-Level Quantum Systems in Two-Dimensional Materials for Single Photon Emission. <i>Nano Letters</i> , 2019, 19, 408-414.	4.5	59
13	Unusual Negative Formation Enthalpies and Atomic Ordering in Isovalent Alloys of Transition Metal Dichalcogenide Monolayers. <i>Chemistry of Materials</i> , 2018, 30, 1547-1555.	3.2	20
14	Design of Lead-Free Inorganic Halide Perovskites for Solar Cells via Cation-Transmutation. <i>Journal of the American Chemical Society</i> , 2017, 139, 2630-2638.	6.6	714
15	Antimony Diffusion in CdTe. <i>IEEE Journal of Photovoltaics</i> , 2017, 7, 870-873.	1.5	11
16	Earth-Abundant and Non-Toxic SiX (X = S, Se) Monolayers as Highly Efficient Thermoelectric Materials. <i>Journal of Physical Chemistry C</i> , 2017, 121, 123-128.	1.5	41
17	Design of Two-Dimensional Graphene-like Dirac Materials $\hat{\Gamma}^{2}XBeB_{5}$ (X = H, F). <i>Journal of Applied Physics</i> , 2017, 121, 074301.	2.1	23
18	Carrier providers or killers: The case of Cu defects in CdTe. <i>Applied Physics Letters</i> , 2017, 111, 042106.	1.5	22

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19	Notice of Removal Antimony diffusion in CdTe. , 2017, , .		0
20	Fast self-diffusion of ions in CH ₃ NH ₃ Pb ₃ : the interstitially mechanism versus vacancy-assisted mechanism. Journal of Materials Chemistry A, 2016, 4, 13105-13112.	5.2	74
21	Phosphorus Diffusion Mechanisms and Deep Incorporation in Polycrystalline and Single-Crystalline CdTe. Physical Review Applied, 2016, 5, .	1.5	26
22	Review on first-principles study of defect properties of CdTe as a solar cell absorber. Semiconductor Science and Technology, 2016, 31, 083002.	1.0	109
23	Chemical Trends of Electronic Properties of Two-Dimensional Halide Perovskites and Their Potential Applications for Electronics and Optoelectronics. Journal of Physical Chemistry C, 2016, 120, 24682-24687.	1.5	41
24	Non-Radiative Carrier Recombination Enhanced by Two-Level Process: A First-Principles Study. Scientific Reports, 2016, 6, 21712.	1.6	74
25	Two-Dimensional SiS Layers with Promising Electronic and Optoelectronic Properties: Theoretical Prediction. Nano Letters, 2016, 16, 1110-1117.	4.5	149
26	Self-regulation of charged defect compensation and formation energy pinning in semiconductors. Scientific Reports, 2015, 5, 16977.	1.6	56
27	First-principles multiple-barrier diffusion theory: The case study of interstitial diffusion in CdTe. Physical Review B, 2015, 91, .	1.1	33
28	Enhanced p-type dopability of P and As in CdTe using non-equilibrium thermal processing. Journal of Applied Physics, 2015, 118, .	1.1	60
29	Halide perovskite materials for solar cells: a theoretical review. Journal of Materials Chemistry A, 2015, 3, 8926-8942.	5.2	1,114
30	Defect properties of Sb- and Bi-doped CuInSe ₂ : The effect of the deep lone-pair <i>s</i> states. Applied Physics Letters, 2014, 105, .	1.5	21
31	Tuning the Fermi level beyond the equilibrium doping limit through quenching: The case of CdTe. Physical Review B, 2014, 90, .	1.1	66
32	What are grain boundary structures in graphene?. Nanoscale, 2014, 6, 4309-4315.	2.8	34
33	Predicting Two-Dimensional Boron-Carbon Compounds by the Global Optimization Method. Journal of the American Chemical Society, 2011, 133, 16285-16290.	6.6	242
34	Compositional dependence of structural and electronic properties of Cu ₂ ZnSn(S,Se) ₄ $\text{Cu}_{2}\text{ZnSn}(\text{S,Se})_{4}$		399
35	Compositional dependence of structural and electronic properties of Sn ₂ Cu ₄ ZnS ₄ $\text{Sn}_{2}\text{Cu}_{4}\text{ZnS}_{4}$		

#	ARTICLE	IF	CITATIONS
37	Effective band gap narrowing of anatase TiO ₂ by strain along a soft crystal direction. Applied Physics Letters, 2010, 96, .	1.5	185
38	Intrinsic point defects and complexes in the quaternary kesterite semiconductor $Cu_{2-x}Zn_xTe$. Physical Review B, 2010, 81, .	1.1	624
39	Electronic structure and phase stability of MgTe, ZnTe, CdTe, and their alloys in the <i>B</i> ₃ , <i>B</i> ₄ , and <i>B</i> ₈ structures. Physical Review B, 2009, 79, .	1.1	55